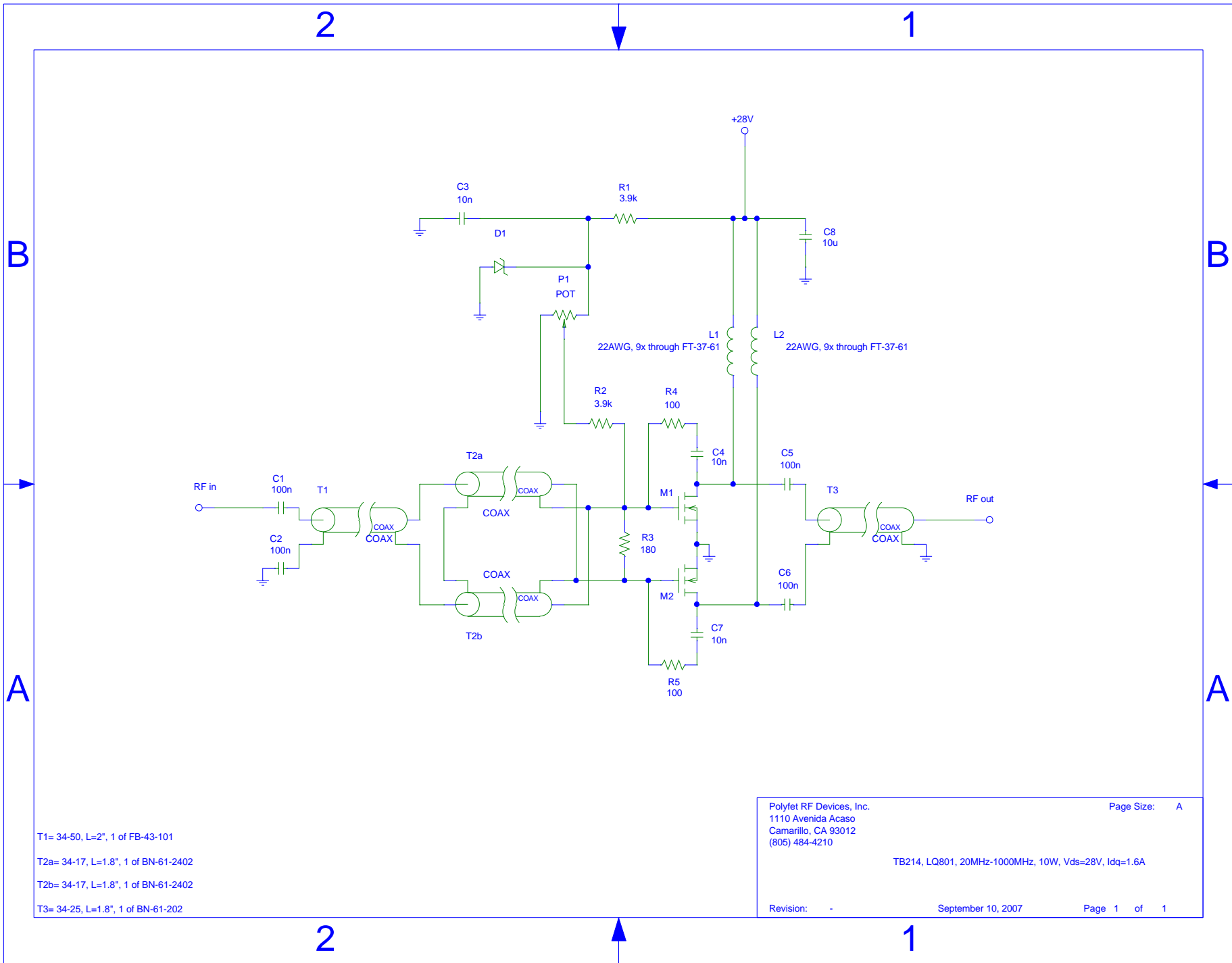


SYMBOL	VALUE	DESCRIPTION
C1, C2, C5, C6	100nF	ATC-200B Chip Cap
C3	10nF	0805 chip cap
C4, C7	10nF	ATC-200B Chip Cap
C8	10uF	50V tantalum
D1	5.6V	Zener Diode
R1	3.9K	0805 chip resistor
R2	9.1k	0805 chip resistor
R3	180	0808 CHP RESISTOR
R4, R5	100	20W Flanged R
T1	2"	UT34-50, 1 of FB-43-101
T2	1.8"	UT34-17, 1 of BN-61-2402
T3	1.8"	UT34-25, 1 of BN-61-202
P1	10k	6mm multi-turn pot
L1, L2	22AWG	9 times through FT-37-61
Q1	LQ801	Polyfet Transistor
Vdd	28V	Drain Voltage
Bias	1.6A	LQ801 bias

DRN BY: Cunningham	09/10/07	POLYFET RF DEVICES		
CHKD :				
ELECT : Cunningham	09/10/07	TB214 LQ801 20-1000MHz 10W 10dB		
MECH : Cunningham	09/10/07	SIZE	FSCM NO	REV
PROC :		Vdd=28V Idq=1.6A		A
QUAL :		SCALE : 1 : 1	SHEET 1	OF 1
PGMS :				



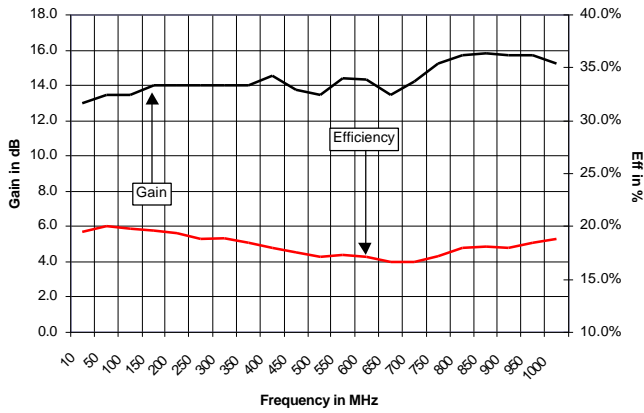
T1= 34-50, L=2", 1 of FB-43-101  
T2a= 34-17, L=1.8", 1 of BN-61-2402  
T2b= 34-17, L=1.8", 1 of BN-61-2402  
T3= 34-25, L=1.8", 1 of BN-61-202

Polyfet RF Devices, Inc.  
1110 Avenida Acaso  
Camarillo, CA 93012  
(805) 484-4210

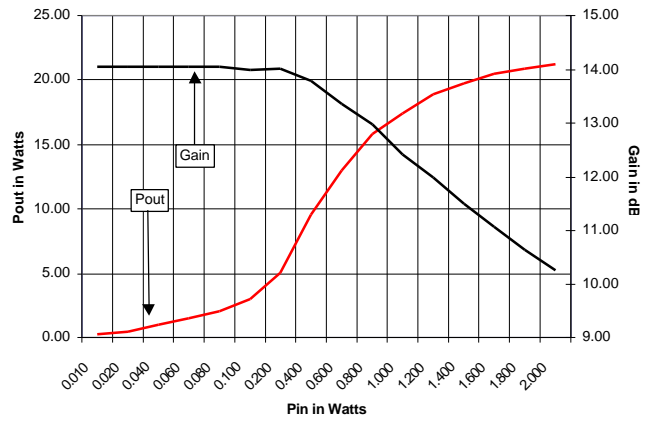
TB214, LQ801, 20MHz-1000MHz, 10W, Vds=28V, Idq=1.6A

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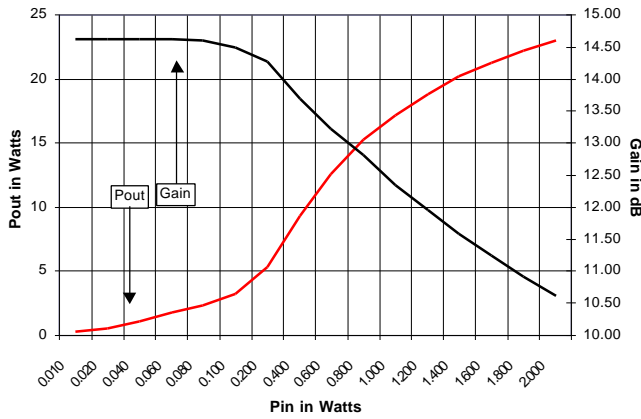
TB214 Gain/Eff vs Freq, Vds=28V, Idq=1.6A Pout=10W



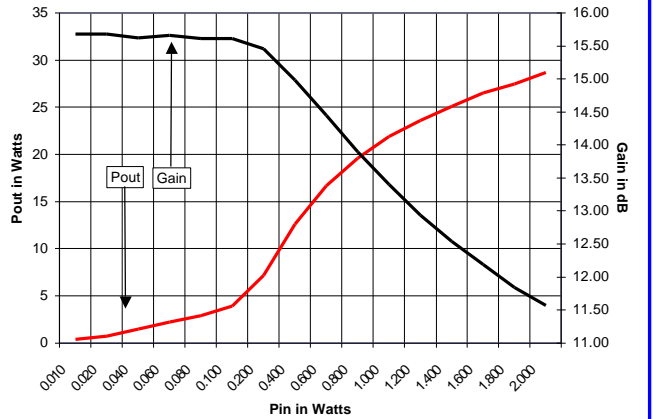
TB214 Pout/Gain vs Pin, Freq=20MHz, Vds=28V, Idq=1.6A



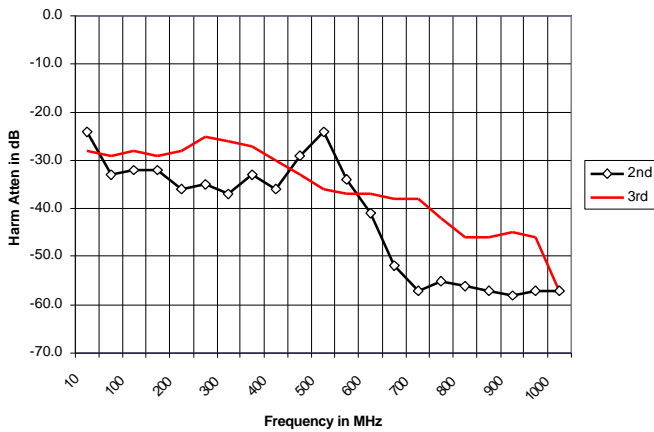
TB214 Pout/Gain vs Pin, Freq=500MHz, Vds=28V, Idq=1.6A



TB214 Pout/Gain vs Pin, Freq=1000MHz, Vds=28V, Idq=1.6A



TB214 Harm vs Freq, Vds=28V, Idq=1.6A, Pout=10W



TB214 IM vs Freq, Vds=28V, Idq=1.6A, PEP=10W

